

NPN SILICON RF POWER TRANSISTOR

DESCRIPTION:

The **ASI UHBS30-1** is Designed for

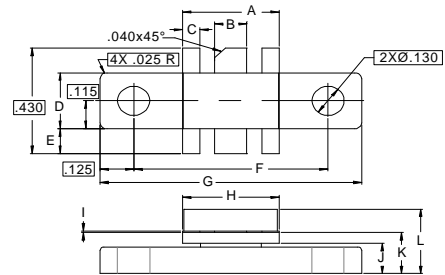
FEATURES:

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- **Omnigold™** Metalization System

MAXIMUM RATINGS

| | |
|---------------|---|
| I_C | 9.0 A |
| V_{CBO} | 50 V |
| V_{CEO} | 30 V |
| V_{EBO} | 4.0 V |
| P_{DISS} | 100 W @ $T_C = 25\text{ }^{\circ}\text{C}$ |
| T_J | $-65\text{ }^{\circ}\text{C}$ to $+200\text{ }^{\circ}\text{C}$ |
| T_{STG} | $-65\text{ }^{\circ}\text{C}$ to $+150\text{ }^{\circ}\text{C}$ |
| θ_{JC} | $1.5\text{ }^{\circ}\text{C/W}$ |

PACKAGE STYLE .230 6L FLG



| DIM | MINIMUM inches / mm | MAXIMUM inches / mm |
|-----|------------------------|------------------------|
| A | .355 / 9.02 | .365 / 9.27 |
| B | .115 / 2.92 | .125 / 3.18 |
| C | .075 / 1.91 | .085 / 2.16 |
| D | .225 / 5.72 | .235 / 5.97 |
| E | .090 / 2.29 | .110 / 2.79 |
| F | .720 / 18.29 | .730 / 18.54 |
| G | .970 / 24.64 | .980 / 24.89 |
| H | .355 / 9.02 | .365 / 9.27 |
| I | .004 / 0.10 | .006 / 0.15 |
| J | .120 / 3.05 | .130 / 3.30 |
| K | .160 / 4.06 | .180 / 4.57 |
| L | .230 / 5.84 | .260 / 6.60 |

ORDER CODE: ASI10670

CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

| SYMBOL | TEST CONDITIONS | MINIMUM | TYPICAL | MAXIMUM | UNITS |
|-------------------|---|---------|---------|---------|---------|
| BV_{CEO} | $I_C = 50\text{ mA}$ | 30 | | | V |
| BV_{CES} | $I_C = 50\text{ mA}$ $R_{BE} = 10\text{ }\Omega$ | 50 | | | V |
| BV_{EBO} | $I_E = 10\text{ mA}$ | 4.0 | | | V |
| I_{CBO} | $V_{CE} = 15\text{ V}$ | | | 5 | mA |
| I_{CES} | $V_{CE} = 24\text{ V}$ | | | 10 | mA |
| h_{FE} | $V_{CE} = 5.0\text{ V}$ $I_C = 1.0\text{ A}$ | 10 | | --- | --- |
| C_{ob} | $V_{CB} = 25\text{ V}$ $f = 1.0\text{ MHz}$ | | | 50 | pF |
| P_G η_c | $V_{CE} = 24\text{ V}$ $P_{OUT} = 30\text{ W}$ $f = 900\text{ GHz}$ | 7.5 | 55 | | dB % |